

TOSHIBA Photocoupler GaAlAs Ired + Photo IC

TLP750

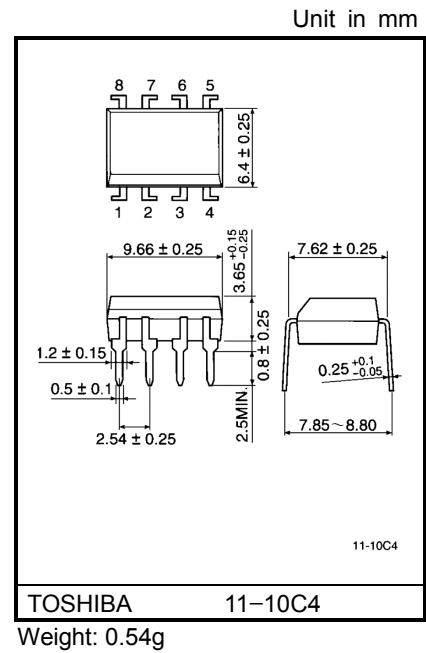
勝特力材料 886-3-5773766
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
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- Digital Logic Ground Isolation
- Line Receiver
- Microprocessor System Interfaces
- Switching Power Supply Feedback Control
- Analog Signal Isolation

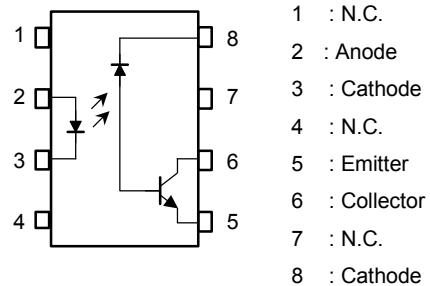
The TOSHIBA TLP750 consists of GaAlAs high-output light emitting diode and a high speed detector of one chip photo diode-transistor. This unit is 8-lead DIP.

TLP750 has no internal base connection, and is suitable for application in noisy environmental conditions.

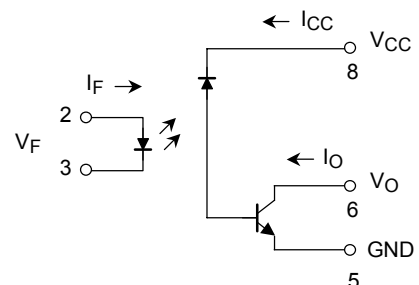
- Switching speed: $t_{pHL}=0.3\mu s$ (typ.)
 - Switching speed: $t_{pLH}=0.5\mu s$ (typ.)($R_L=1.9k\Omega$)
 - UL recognized: UL1577, file No. E67349
 - BSI approved: BS EN60065: 1994,
 Certificate No.7613
 BS EN60950: 1992,
 Certificate No.7614
 - Isolation voltage: $5000V_{rms}$ (min.)
 - Option(d4)type
 VDE approved: DIN VDE0884/06.92,
 Certificate No.68384
 Maximum operating insulation voltage: 890V_{PK}
 Highest permissible over voltage: 8000V_{PK}
- (Note) When a VDE0884 approved type is needed, please designate the "Option(D4)"**
- Creepage distance: 6.4mm(min.)
 Clearance: 6.4mm(min.)
 Insulation thickness: 0.4mm(min.)



Pin Configuration (top view)



Schematic



Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current (Note 1)	I_F	25	mA
	Pulse forward current (Note 2)	I_{FP}	50	mA
	Peak transient forward current (Note 3)	I_{FPT}	1	A
	Reverse voltage	V_R	5	V
	Diode power dissipation (Note 4)	P_D	45	mW
Detector	Output current	I_O	8	mA
	Peak output current	I_{OP}	16	mA
	Output voltage	V_O	-0.5~15	V
	Supply voltage	V_{CC}	-0.5~15	V
	Output power dissipation (Note 5)	P_O	100	mW
Operating temperature range		T_{opr}	-55~100	°C
Storage temperature range		T_{stg}	-55~125	°C
Lead solder temperature(10s) (Note 6)		T_{sol}	260	°C
Isolation voltage (AC, 1min., R.H=60%) (Note 7)		BV_S	5000	V_{rms}

(Note 1) Derate 0.8mA / °C above 70°C.

(Note 2) 50% duty cycle, 1ms pulse width.
Derate 1.6mA / °C above 70°C.

(Note 3) Pulse width ≤ 1μs, 300pps.

(Note 4) Derate 0.9mW / °C above 70°C.

(Note 5) Derate 2mW / °C above 70°C.

(Note 6) Soldering portion of lead: Up to 2mm from the body of the device.

(Note 7) Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together and pins 5, 6, 7 and 8 shorted together.

Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition		Min.	Typ.	Max.	Unit	
LED	Forward voltage	V_F	$I_F=16\text{mA}$		—	1.65	1.85	V	
	Forward voltage temperature coefficient	$\Delta V_F / \Delta T_a$	$I_F=16\text{mA}$		—	-2	—	mV / °C	
	Reverse current	I_R	$V_R=5\text{V}$		—	—	10	μA	
	Capacitance between terminal	C_T	$V_F=0, f=1\text{MHz}$		—	45	—	pF	
Detector	High level output current	$I_{OH(1)}$	$I_F=0\text{mA}, V_{CC}=V_O=5.5\text{V}$		—	3	500	nA	
		$I_{OH(2)}$	$I_F=0\text{mA}, V_{CC}=V_O=15\text{V}$		—	—	5	μA	
		I_{OH}	$I_F=0\text{mA}, V_{CC}=V_O=15\text{V}$ $T_a=70^\circ\text{C}$		—	—	50	μA	
	High level supply voltage	I_{CCH}	$I_F=0\text{mA}, V_{CC}=15\text{V}$		—	0.01	1	μA	
Coupled	Current transfer ratio	I_O/I_F	$I_F=16\text{mA}$ $V_{CC}=4.5\text{V}$ $V_O=0.4\text{V}$	$T_a=25^\circ\text{C}$	10	30	—	%	
				Rank: 0	19	30	—		
				$T_a=0\sim 70^\circ\text{C}$	5	—	—		
	Low level output voltage	V_{OL}	$I_F=16\text{mA}, V_{CC}=4.5\text{V},$ $I_O=1.1\text{mA}$ (rank 0: $I_O=2.4\text{mA}$)			—	—	0.4	V
						—	—	—	—
Isolation resistance	R_S	$R.H.=60\%, V=5000\text{V}_{DC}$		(Note 7)	1×10^{12}	10^{14}	—	Ω	
Capacitance between input to output	C_S	$V_S=0, f=1\text{MHz}$		(Note 8)	—	0.8	—	pF	

Switching Characteristics (Ta = 25°C, Vcc = 5V)

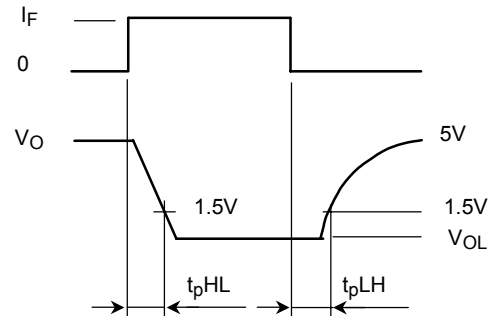
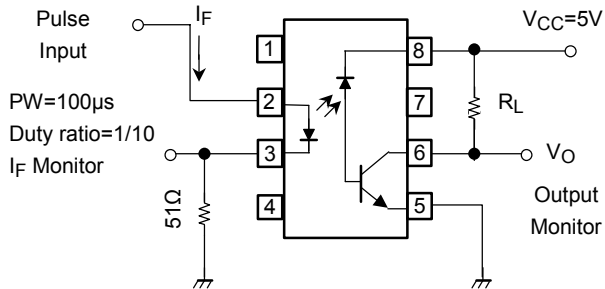
Characteristic	Symbol	Test Circuit	Test Condition	Min.	Typ.	Max.	Unit
Propagation delay time (H→L)	t_{pHL}	1	$I_F=0 \rightarrow 16\text{mA}, V_{CC}=5\text{V},$ $R_L=4.1\text{k}\Omega$	—	0.2	0.8	μs
			Rank 0: $R_L=1.9\text{k}\Omega$	—	0.3	0.8	
Propagation delay time (L→H)	t_{pLH}	1	$I_F=16 \rightarrow 0\text{mA}, V_{CC}=5\text{V},$ $R_L=4.1\text{k}\Omega$	—	1.0	2.0	μs
			Rank 0: $R_L=1.9\text{k}\Omega$	—	0.5	1.2	
Common mode transient immunity at logic high output (Note 8)	C_{MH}	2	$I_F=0\text{mA}, V_{CM}=200\text{V}_{p-p}$ $R_L=4.1\text{k}\Omega$ (Rank 0: $R_L=1.9\text{k}\Omega$)	—	1500	—	V / μs
Common mode transient immunity at logic low output (Note 8)	C_{ML}		$I_F=16\text{mA}, V_{CM}=200\text{V}_{p-p}$ $R_L=4.1\text{k}\Omega$ (Rank 0: $R_L=1.9\text{k}\Omega$)	—	-1500	—	V / μs

(Note 8) CML is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state ($V_O < 0.8V$).

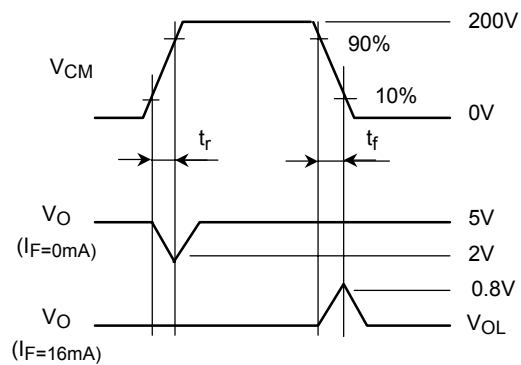
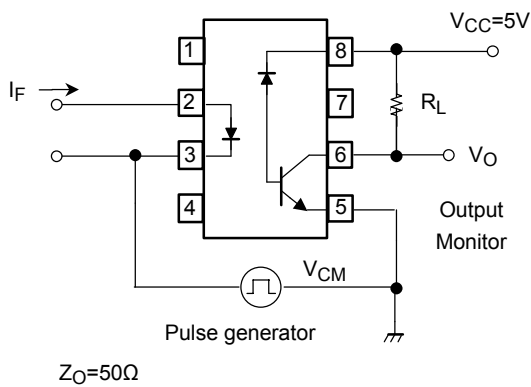
CMH is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic high state ($V_O > 2.0V$).

(Note 9) Maximum electrostatic discharge voltage for any pins: 100V(C=200pF, R=0)

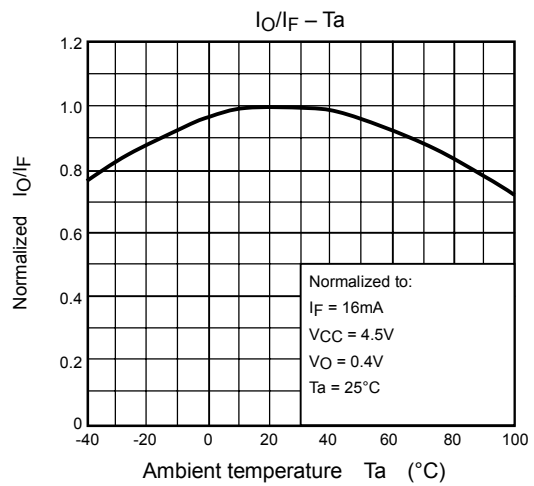
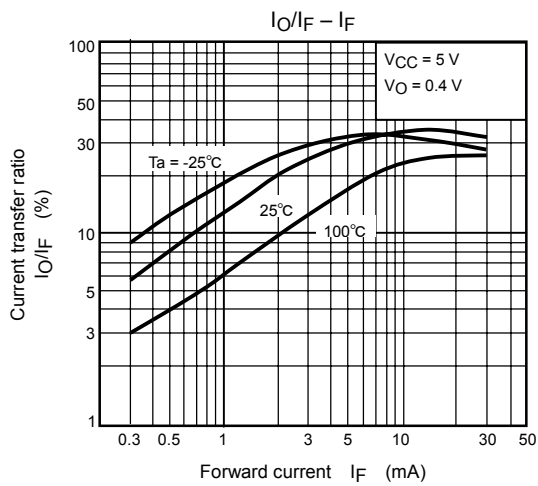
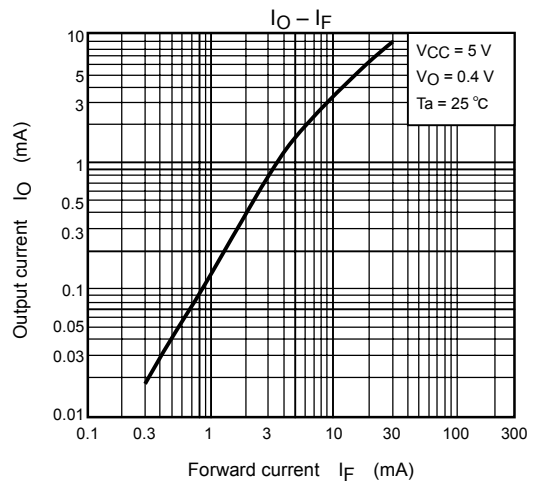
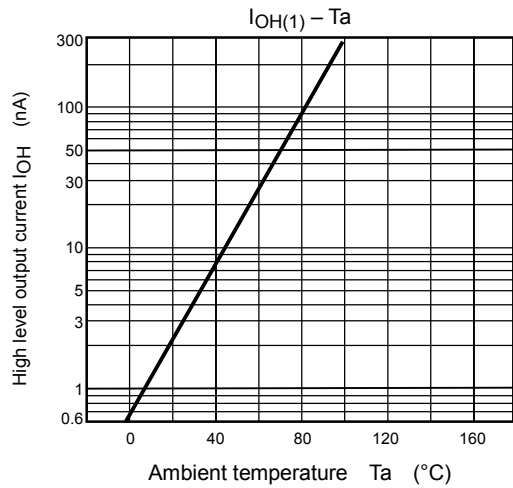
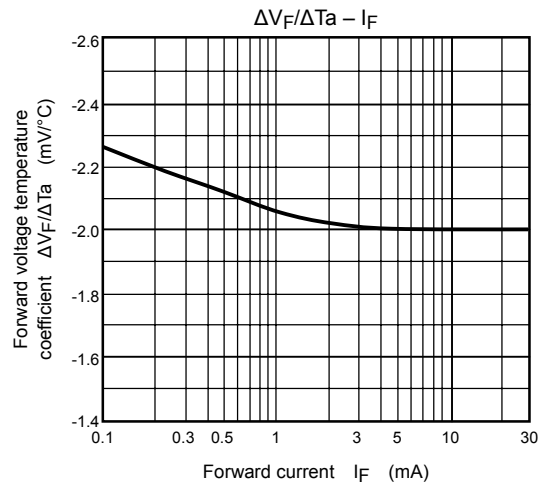
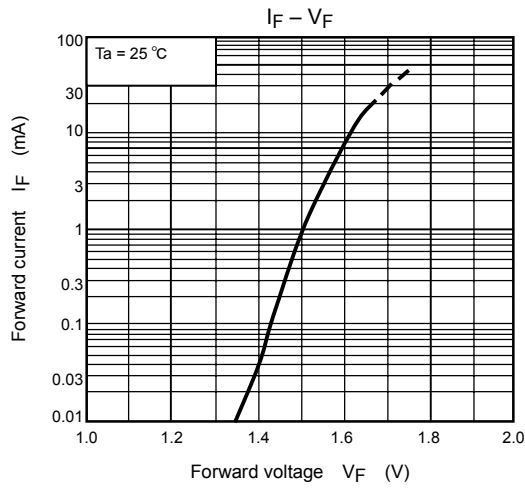
Test Circuit 1: Switching Time Test Circuit

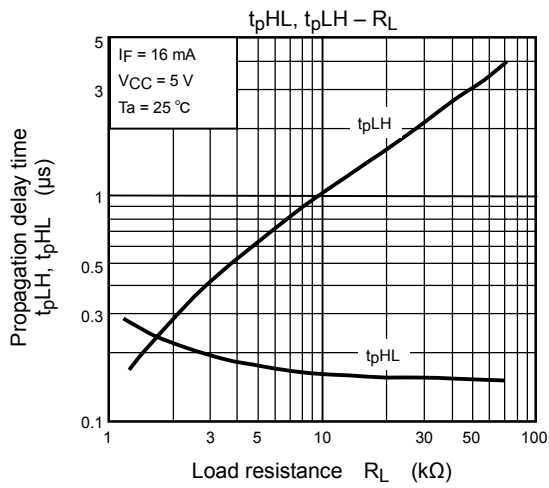
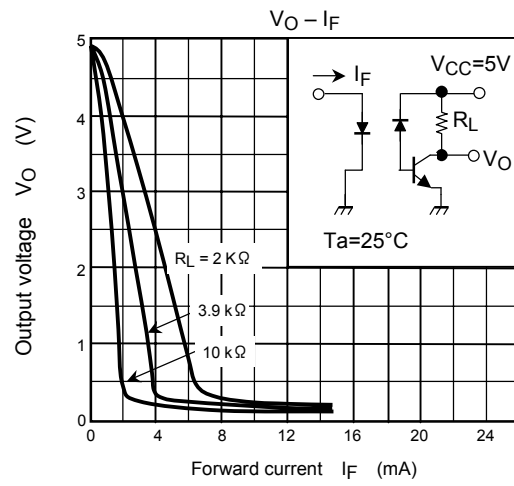
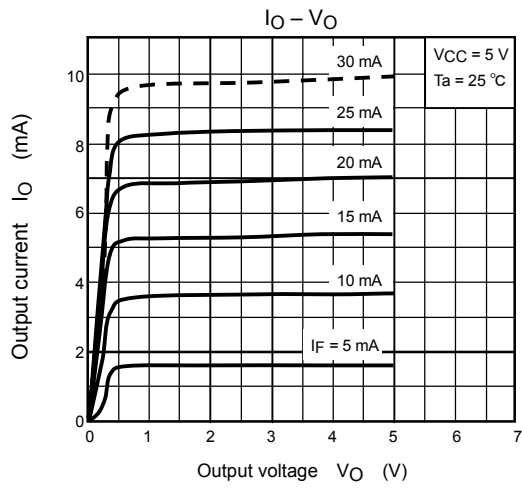


Test Circuit 2: Common Mode Noise Immunity Test Circuit



$$CM_H = \frac{160(V)}{t_r(\mu s)}, CM_L = \frac{160(V)}{t_f(\mu s)}$$





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